NXP USA Inc. - MPC8358EVRAGDGA Datasheet

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8358evragdga

    - ATM (AAL2/AAL5) to Ethernet (IP) interworking in accordance with RFC2684 including bridging of ATM ports to Ethernet ports
    - Extensive support for ATM statistics and Ethernet RMON/MIB statistics
    - AAL2 protocol rate up to 4 CPS at OC-3/STM-1 rate
    - Packet over Sonet (POS) up to 622-Mbps full-duplex 124 MultiPHY
    - POS hardware; microcode must be loaded as an IRAM package
    - Transparent up to 70-Mbps full-duplex
    - HDLC up to 70-Mbps full-duplex
    - HDLC BUS up to 10 Mbps
    - Asynchronous HDLC
    - UART
    - BISYNC up to 2 Mbps
    - User-programmable Virtual FIFO size
    - QUICC multichannel controller (QMC) for 64 TDM channels
  - One UTOPIA/POS interface on the MPC8358E supporting 31/124 MultiPHY
  - Two serial peripheral interfaces (SPI); SPI2 is dedicated to Ethernet PHY management
  - Four TDM interfaces on the MPC8358E with 1-bit mode for E3/T3 rates in clear channel
  - Sixteen independent baud rate generators and 30 input clock pins for supplying clocks to UCC serial channels
  - Four independent 16-bit timers that can be interconnected as four 32-bit timers
  - Interworking functionality:
    - Layer 2 10/100-Base T Ethernet switch
    - ATM-to-ATM switching (AAL0, 2, 5)
    - Ethernet-to-ATM switching with L3/L4 support
    - PPP interworking
- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs).
  - Public key execution unit (PKEU) supporting the following:
    - RSA and Diffie-Hellman
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard execution unit (DEU)
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	−0.3 to 1.32	V	—
PLL supply voltage		AV_{DD}	−0.3 to 1.32	V	—
DDR and DDR2 DRAM I/O voltage DDR DDR2		GV_{DD}	 −0.3 to 2.75 −0.3 to 1.89	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	−0.3 to 3.63	V	—
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage		OV_{DD}	−0.3 to 3.63	V	—
Input voltage	DDR DRAM signals	MV_{IN}	−0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	−0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	−0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	−0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	−0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	−55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** **MV_{IN}** must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode)[1]	GV_{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)[1]	GV_{DD} = 1.8 V
10/100/1000 Ethernet signals	42	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V LV_{DD} = 2.5/3.3 V

[1] DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8358E.

2.2.1 Power-Up Sequencing

MPC8358E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

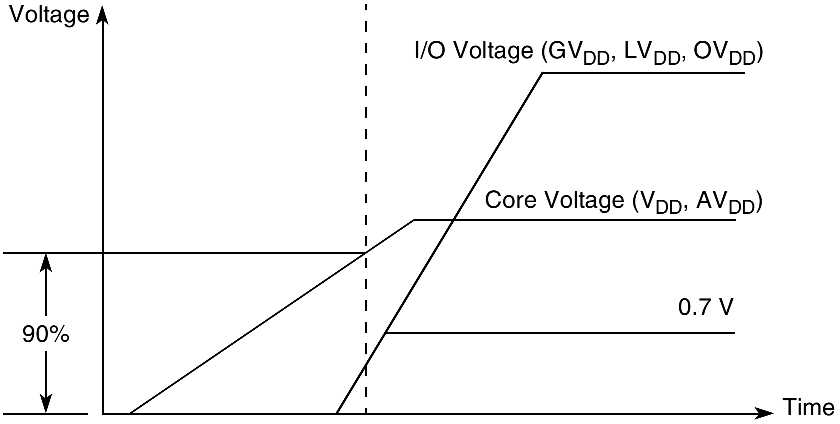


Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

2.2.2 Power-Down Sequencing

The MPC8358E does not require the core supply voltage and I/O supply voltages to be powered down in any particular order.

3 Power Characteristics

The estimated typical power dissipation values are shown in Table 4.

Table 4. MPC8358E PBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	266	2.2	2.3	W	2, 3, 4
400	266	266	2.4	2.5	W	2, 3, 4
400	266	400	2.5	2.6	W	2, 3, 4

Notes:

1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.
2. Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3. Thermal solutions will likely need to design to a value higher than typical power on the end application, T_A target, and I/O power.
4. Maximum power is based on a voltage of V_{DD} = 1.2 V, WC process, a junction T_J = 105°C, and an artificial smoke test.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications Mode

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
MDQS—MDQ/MECC input skew per byte 266 MHz 200 MHz	t_{DISKEW}	 –1125 –1250	 1125 1250	ps	1, 2

Notes:

1. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
2. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 ≤ n ≤ 7) or ECC (MECC[{0...7}] if n = 8).

Figure 5 shows the input timing diagram for the DDR controller.

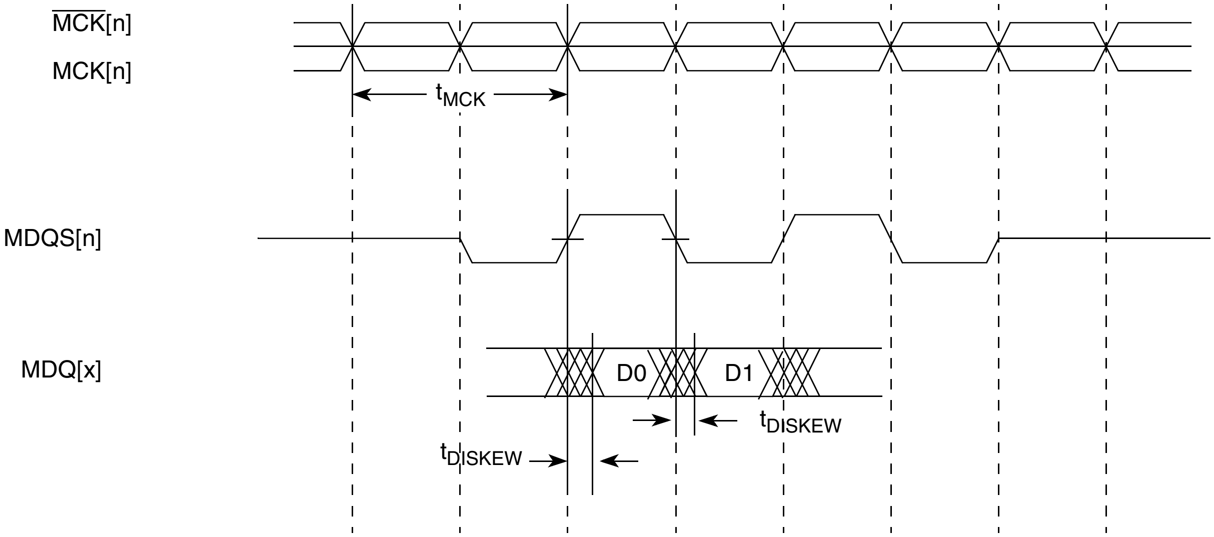


Figure 5. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 and Table 21 provide the output AC timing specifications and measurement conditions for the DDR and DDR2 SDRAM interface.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{MCK}$[n] crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 266 MHz 200 MHz	t_{AOSKEW}	 –1.1 –1.2	 0.3 0.4	ns	3

Table 37. IEEE 1588 Timer AC Specifications (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Timer alarm to output valid	t_{TMRAL}	—	—	—	2

Notes:

1. The timer can operate on rtc_clock or tmr_clock. These clocks get muxed and any one of them can be selected. The minimum and maximum requirement for both rtc_clock and tmr_clock are the same.
2. These are asynchronous signals.
3. Inputs need to be stable at least one TMR clock.

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8358E.

9.1 Local Bus DC Electrical Characteristics

Table 38 provides the DC electrical characteristics for the local bus interface.

Table 38. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	µA

9.2 Local Bus AC Electrical Specifications

Table 39 describes the general timing parameters of the local bus interface of the device.

Table 39. Local Bus General Timing Parameters—DLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.7	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3.0	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

Table 42 provides the JTAG AC timing specifications as defined in Figure 29 through Figure 32.

Table 42. JTAG AC Timing Specifications (Independent of CLKIN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JTKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	 5, 6 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 21). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Figure 28 provides the AC test load for TDO and the boundary-scan outputs of the device.

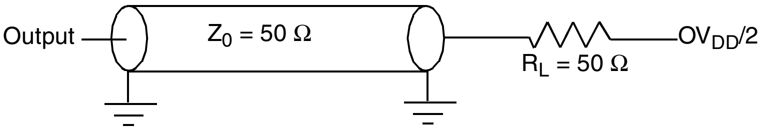
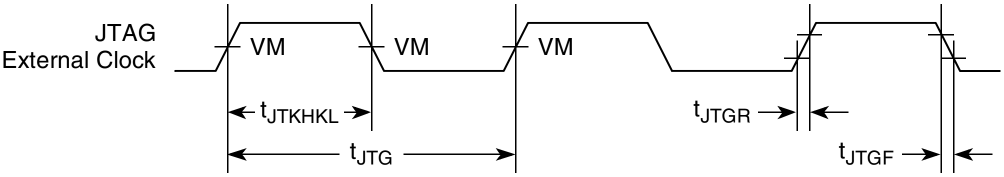


Figure 28. AC Test Load for the JTAG Interface

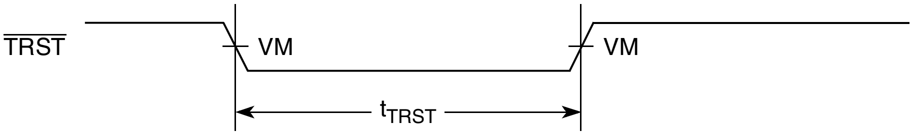
Figure 29 provides the JTAG clock input timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 29. JTAG Clock Input Timing Diagram

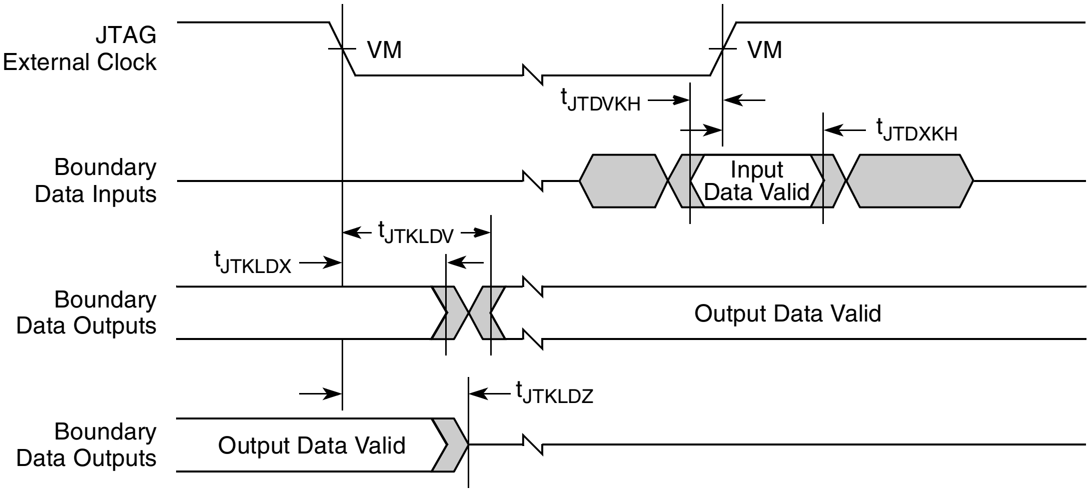
Figure 30 provides the $\overline{\text{TRST}}$ timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 30. $\overline{\text{TRST}}$ Timing Diagram

Figure 31 provides the boundary-scan timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 31. Boundary-Scan Timing Diagram

11 I^2C

This section describes the DC and AC electrical characteristics for the I^2C interface of the MPC8358E.

11.1 I^2C DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the I^2C interface of the device.

Table 43. I^2C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	C_I	—	10	pF	—
Input current ($0 V \leq V_{IN} \leq OV_{DD}$)	I_{IN}	—	±10	μA	4

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8360E Integrated Communications Processor Family Reference Manual* for information on the digital filter used.
4. I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

11.2 I^2C AC Electrical Specifications

Table 44 provides the AC timing parameters for the I^2C interface of the device.

Table 44. I^2C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 43).

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns

Table 47. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	7.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0.3	—	ns	2, 4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

Figure 35 provides the AC test load for PCI.

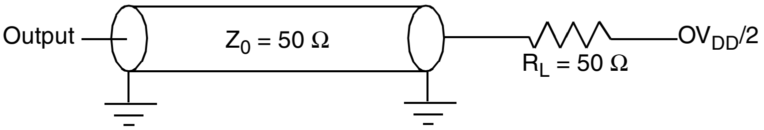


Figure 35. PCI AC Test Load

Figure 36 shows the PCI input AC timing conditions.

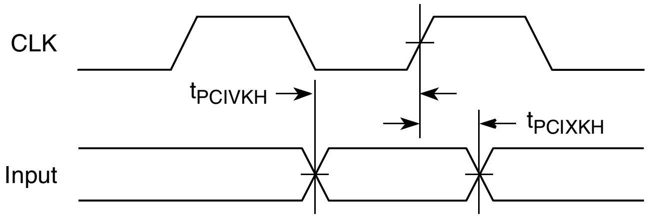


Figure 36. PCI Input AC Timing Measurement Conditions

Figure 39 provides the AC test load for the GPIO.

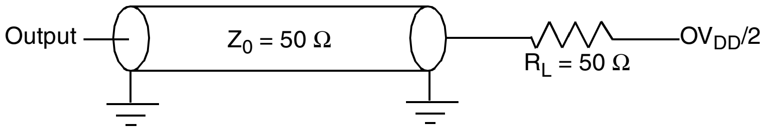


Figure 39. GPIO AC Test Load

15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8358E.

15.1 IPIC DC Electrical Characteristics

Table 52 provides the DC electrical characteristics for the external interrupt pins of the IPIC.

Table 52. IPIC DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	μA
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, $\overline{\text{MCP\_OUT}}$, and CE ports Interrupts.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

15.2 IPIC AC Timing Specifications

Table 53 provides the IPIC input and output AC timing specifications.

Table 53. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

16 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8358E.

16.1 SPI DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the device SPI.

Table 54. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = –6.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0$ mA	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	±10	μA

16.2 SPI AC Timing Specifications

Table 55 and provide the SPI input and output AC timing specifications.

Table 55. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOX} t_{NIKHOV}	0.4 —	— 8	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOX} t_{NEKHOV}	2 —	— 8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	8	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 40 provides the AC test load for the SPI.

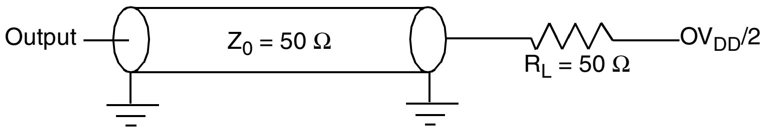


Figure 40. SPI AC Test Load

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8358E.

20.1 USB DC Electrical Characteristics

Table 63 provides the DC electrical characteristics for the USB interface.

Table 63. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	μA

20.2 USB AC Electrical Specifications

Table 64 describes the general timing parameters of the USB interface of the device.

Table 64. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at OV_{DD}/2 of the rising or falling edge of the signals.

Figure 51 provide the AC test load for the USB.

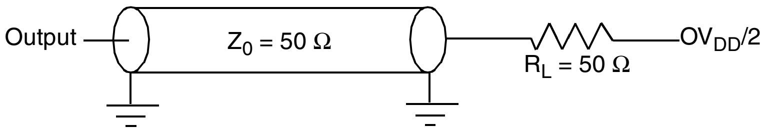


Figure 51. USB AC Test Load

21 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8358E is available in a plastic ball grid array (PBGA), see Section 21.1, "Package Parameters for the PBGA Package," and Section 21.2, "Mechanical Dimensions of the PBGA Package," for information on the package.

21.1 Package Parameters for the PBGA Package

The package parameters for rev 2.0 silicon are as provided in the following list. The package type is **29** mm x 29 mm, 668 plastic ball grid array (PBGA).

Package outline	**29 mm x 29 mm**
Interconnects	**668**
Pitch	**1.00 mm**
Module height (typical)	1.46 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZQ package)
	95.5 Sn/0.5 Cu/4Ag (VR package)
Ball diameter (typical)	0.64 mm

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TDI	AE8	I	OV_{DD}	4
TDO	AG7	O	OV_{DD}	3
TMS	AH7	I	OV_{DD}	4
$\overline{TRST}$	AG8	I	OV_{DD}	4
Test				
TEST	AF9	I	OV_{DD}	7
$\overline{TEST\_SEL}$	AE27	I	GV_{DD}	9
PMC				
$\overline{QUIESCE}$	AF4	O	OV_{DD}	—
System Control				
$\overline{PORESET}$	AE9	I	OV_{DD}	—
$\overline{HRESET}$	AG9	I/O	OV_{DD}	1
$\overline{SRESET}$	AH10	I/O	OV_{DD}	2
Thermal Management				
THERM0	K25	I	GV_{DD}	—
THERM1	AA26	I	GV_{DD}	—
Power and Ground Signals				
$AV_{DD}1$	AF8	Power for LBIU DLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	AH8	Power for CE PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}5$	AB26	Power for e300 PLL (1.2 V)	$AV_{DD}5$	—
$AV_{DD}6$	AH9	Power for system PLL (1.2 V)	$AV_{DD}6$	—
GND	C16, D11, D21, E24, F7, J10, J12, J15, J16, J17, J28, K11, K13, K14, K17, K18, L4, L9, L11, L12, L13, L14, L15, L16, L17, L18, L19, L24, M10, M11, M14, M15, M18, M19, N11, N18, N25, P9, P11, P18, P19, R9, R11, R14, R15, R18, R19, R26, T10, T11, T14, T15, T18, T25, U10, U11, U18, V9, V11, V14, V15, V18, V24, V27, W18, W19, Y11, Y14, Y18, Y19, Y25, Y27, AB4, AB27, AC27, AE20, AE24, AF5, AF15, AG10	—	—	—

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV_{DD}	C19, C22, C25, G24, J18, J19, J20, J24, K19, K20, K26, L20, M20, M26, N19, N20, P20, P27, R20, T19, T20, T27, U19, U20, U25, V19, V20, W20, W26, Y20, AA24, AB28, AC21, AC28, AD28, AF21, AF25	Power for DDR DRAM I/O Voltage (2.5 V or 1.8 V)	GV_{DD}	—
$LV_{DD}0$	F3, J9	—	$LV_{DD}0$	—
$LV_{DD}1$	P3, P10	—	$LV_{DD}1$	10
$LV_{DD}2$	R4, R10	—	$LV_{DD}2$	10
V_{DD}	M12, M13, M16, M17, N10, N12, N13, N14, N15, N16, N17, P12, P13, P14, P15, P16, P17, R12, R13, R16, R17, T12, T13, T16, T17, U12, U13, U14, U15, U16, U17, V12, V13, V16, V17, W11, W12, W13, W15, W16, W17, Y16, Y17	Power for Core (1.2 V)	V_{DD}	—
OV_{DD}	C6, C12, D17, J11, J13, J14, K3, K9, K10, K12, K15, K16, L10, M9, N9, T9, U9, V3, V10, W9, W10, W14, Y9, Y10, Y12, Y13, Y15, AA3, AE6, AE16, AF11, AF20	PCI, 10/100 Ethernet, and other Standard (3.3 V)	OV_{DD}	—
MVREF1	J27	I	DDR Reference Voltage	—
MVREF2	Y24	I	DDR Reference Voltage	—
No Connect				
NC	F23, G23, H23, J23, K23, L23, M23, N23, P23, R23, T23, U23, V23, W23, Y23, AA23, AB23, AC23	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 kΩ) should be placed on this pin to OV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 kΩ) should be placed on this pin to OV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. This pin must always be tied to GV_{DD}.
10. Refers to *MPC8360E PowerQUICC II™ Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins” for information about the two UCC2 Ethernet interface options.
11. It is recommended that MDIC0 be tied to GND using an 18.2 Ω resistor and MDIC1 be tied to DDR power using an 18.2 Ω resistor for DDR2.

Note that *lb_clk* is not the external local bus or DDRC2 frequency; *lb_clk* passes through the a LB clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LB clock divider ratio is controlled by LCRR[CLKDIV].

In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset. Table 66 specifies which units have a configurable clock frequency.

Table 66. Configurable Clock Units

Unit	Default Frequency	Options
Security core	*csb_clk*/3	Off, *csb_clk*[1], *csb_clk*/2, *csb_clk*/3
PCI and DMA complex	csb_clk	Off, *csb_clk*

[1] With limitation, only for slow csb_clk rates, up to 166 MHz.

Table 67 provides the operating frequencies for the PBGA package under recommended operating conditions (see Table 2). All frequency combinations shown in the table below may not be available. Maximum operating frequencies depend on the part ordered, see Section 25.1, “Part Numbers Fully Addressed by this Document,” for part ordering details and contact your Freescale sales representative or authorized distributor for more information.

Table 67. Operating Frequencies for the PBGA Package

Characteristic[1]	400 MHz	Unit
e300 core frequency (*core_clk*)	266–400	MHz
Coherent system bus frequency (*csb_clk*)	133–266	MHz
QUICC Engine frequency (*ce_clk*)	266–400	MHz
DDR and DDR2 memory bus frequency (MCLK)[2]	100–133	MHz
Local bus frequency (LCLK*n*)[3]	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66.67	MHz
Security core maximum internal operating frequency	133	MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.

[2] The DDR data rate is 2x the DDR memory bus frequency.

[3] The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBCM]).

22.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. Table 68 shows the multiplication factor encodings for the system PLL.

Table 68. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in Table 69.

Table 69. System PLL VCO Divider

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

The system VCO frequency is derived from the following equations:

- *csb_clk* = {PCI_SYNC_IN × (1 + CFG_CLKIN_DIV)} × SPMF
- System VCO Frequency = *csb_clk* × VCO divider (if both RCWL[DDRCM] and RCWL[LBCM] are cleared)
  OR
- System VCO frequency = 2 × *csb_clk* × VCO divider (if either RCWL[DDRCM] or RCWL[LBCM] are set).

As described in Section 22, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 70 shows the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 70. CSB Frequency Options

CFG_CLKIN_DIV at Reset[1]	**SPMF**	***csb_clk*: Input Clock Ratio**[2]	**Input Clock Frequency (MHz)**[2]			
			16.67	**25**	**33.33**	**66.67**
			***csb_clk* Frequency (MHz)**			
Low	0010	2:1				133
Low	0011	3:1			100	200
Low	0100	4:1		100	133	266
Low	0101	5:1		125	166	333
Low	0110	6:1	100	150	200	
Low	0111	7:1	116	175	233	
Low	1000	8:1	133	200	266	
Low	1001	9:1	150	225	300	
Low	1010	10:1	166	250	333	
Low	1011	11:1	183	275		
Low	1100	12:1	200	300		
Low	1101	13:1	216	325		
Low	1110	14:1	233			
Low	1111	15:1	250			
Low	0000	16:1	266			
High	0010	2:1				133
High	0011	3:1			100	200
High	0100	4:1			133	266
High	0101	5:1			166	333

23.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J – T_A$) are possible.

23.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package will be approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device. At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (°C)
T_B = board temperature at the package perimeter (°C)
$R_{\theta JA}$ = junction to board thermal resistance (°C/W) per JESD51-8
P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.